



America Semiconductor

Silicon Fast Recovery Diode

1N3879 thru
1N3883R

$V_{RRM} = 50\text{ V} - 400\text{ V}$

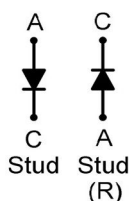
$I_F = 6\text{ A}$

Features

- High Surge Capability
- Types up to 400 V V_{RRM}

Note:

1. Standard polarity: Stud is cathode.
2. Reverse polarity (R): Stud is anode.
3. Stud is base.



DO-4 Package



Maximum ratings, at $T_j = 25\text{ }^{\circ}\text{C}$, unless otherwise specified ("R" devices have leads reversed)

Parameter	Symbol	Conditions	1N3879 (R)	1N3880 (R)	1N3881 (R)	1N3882 (R)	1N3883 (R)	Unit
Repetitive peak reverse voltage	V_{RRM}		50	100	200	300	400	V
RMS reverse voltage	V_{RMS}		35	70	140	210	280	V
DC blocking voltage	V_{DC}		50	100	200	300	400	V
Continuous forward current	I_F	$T_C \leq 100\text{ }^{\circ}\text{C}$	6	6	6	6	6	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25\text{ }^{\circ}\text{C}$, $t_p = 8.3\text{ ms}$	90	90	90	90	90	A
Operating temperature	T_j		-65 to 150	-65 to 150	-65 to 150	-65 to 150	-65 to 150	$^{\circ}\text{C}$
Storage temperature	T_{stg}		-65 to 175	-65 to 175	-65 to 175	-65 to 175	-65 to 175	$^{\circ}\text{C}$

Electrical characteristics, at $T_j = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	1N3879 (R)	1N3880 (R)	1N3881 (R)	1N3882 (R)	1N3883 (R)	Unit
Diode forward voltage	V _F	I _F = 6 A, T _j = 25 °C	1.4	1.4	1.4	1.4	1.4	V
Reverse current	I _R	V _R = 50 V, T _j = 25 °C	15	15	15	15	15	μA
		V _R = 50 V, T _j = 150 °C	3	3	3	3	3	mA
Recovery Time								
Maximum reverse recovery time	T _{RR}	I _F =0.5 A, I _R =1.0 A, I _{RR} = 0.25 A	200	200	200	200	200	nS
Thermal characteristics								
Thermal resistance, junction - case	R _{thJC}		2.5	2.5	2.5	2.5	2.5	°C/W



